

**WHAT IS CLAIMED IS:**

1. A metal plating method comprising:  
preparing an acidic pretreatment agent by  
reacting or mixing in advance a palladium compound with  
a silane-coupling agent obtained by reacting an  
imidazole-based compound and an epoxysilane-based  
compound;  
treating the surface of an object to be plated  
with said pretreatment agent; and  
then electroless plating said plating object.
2. The metal plating method according to claim 1,  
wherein said object is a semiconductor wafer.
3. The metal plating method according to claim 1,  
wherein said electroless plating is a copper or nickel  
electroless plating.
4. The metal plating method according to claim 3,  
wherein a conductive layer is formed by said copper or  
nickel electroless plating, and a copper is  
electroplated on said conductive layer.
5. A metal plating pretreatment agent comprising a  
solution obtained by reacting or mixing in advance a  
palladium compound with a silane-coupling agent  
obtained by reacting an imidazole-based compound and an  
epoxysilane-based compound.
6. A semiconductor wafer, whereon a metal plating  
layer been formed with the metal plating method  
according to claim 1.
7. A semiconductor device using the semiconductor  
wafer according to claim 6.